

# SSM1N45B

## 450V N-Channel MOSFET

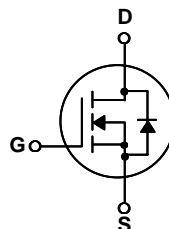
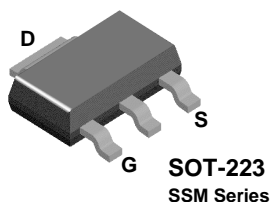
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic ballasts based on half bridge configuration.

### Features

- 0.5A, 450V,  $R_{DS(on)} = 4.25\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 6.5 nC)
- Low Crss ( typical 6.5 pF)
- 100% avalanche tested
- Improved dv/dt capability
- Gate-Source Voltage  $\pm 50V$  guaranteed



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	SSM1N45B	Units
V <sub>DSS</sub>	Drain-Source Voltage	450	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	0.5	A
		0.32	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	4.0	A
V <sub>GSS</sub>	Gate-Source Voltage	± 50	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	108	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	0.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	0.25	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C)	0.9	W
	Power Dissipation (T <sub>L</sub> = 25°C) - Derate above 25°C	2.5	W
		0.02	W/°C
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 6b)	--	63	°C/W

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	450	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.5	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 450\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 360\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 50\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -50\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.3	3.0	3.7	V
		$V_{DS} = V_{GS}, I_D = 250\text{ mA}$	3.5	4.2	4.9	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.25\text{ A}$	--	3.4	4.25	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.25\text{ A}$ (Note 4)	--	0.7	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	185	240	pF
$C_{oss}$	Output Capacitance		--	29	40	pF
$C_{riss}$	Reverse Transfer Capacitance		--	6.5	8.5	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 225\text{ V}, I_D = 0.5\text{ A},$ $R_G = 25\ \Omega$  (Note 4,5)	--	7.5	25	ns
$t_r$	Turn-On Rise Time		--	21	50	ns
$t_{d(off)}$	Turn-Off Delay Time		--	23	55	ns
$t_f$	Turn-Off Fall Time		--	36	80	ns
$Q_g$	Total Gate Charge	$V_{DS} = 360\text{ V}, I_D = 0.5\text{ A},$ $V_{GS} = 10\text{ V}$  (Note 4,5)	--	6.5	8.5	nC
$Q_{gs}$	Gate-Source Charge		--	0.9	--	nC
$Q_{gd}$	Gate-Drain Charge		--	3.2	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	0.5	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	4.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.5\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 0.5\text{ A},$	--	102	--	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.26	--	$\mu\text{C}$

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 75\text{ mH}, I_{AS} = 1.6\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 0.5\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature
6. a) Reference point of the  $R_{\theta JL}$  is the drain lead  
b) When mounted on the minimum pad size recommended (PCB Mount)  
( $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance.  $R_{\theta CA}$  is determined by the user's board design)

## Typical Characteristics

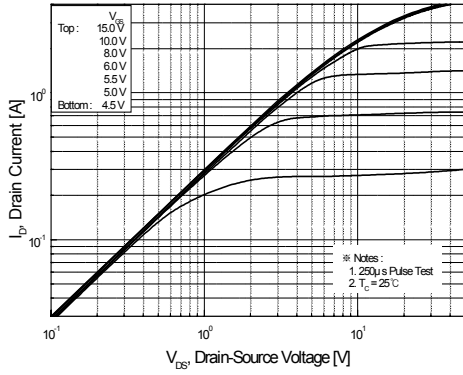


Figure 1. On-Region Characteristics

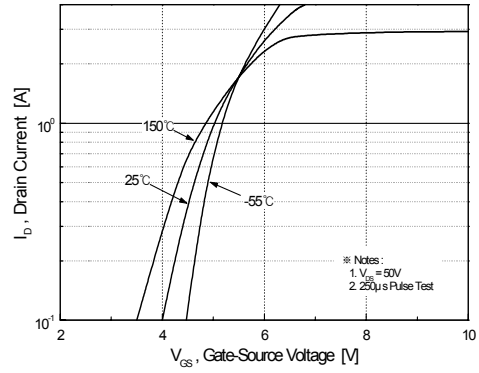


Figure 2. Transfer Characteristics

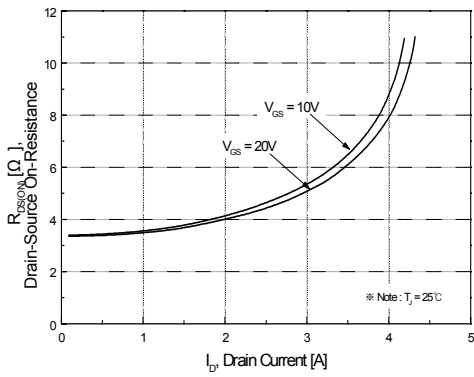


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

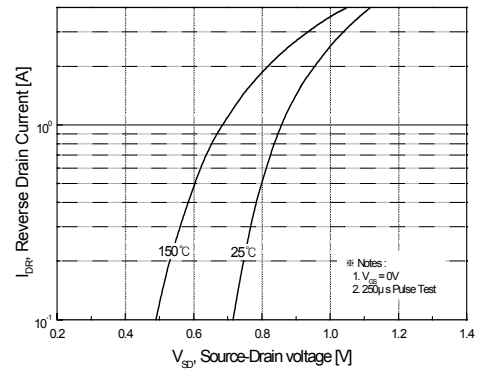


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

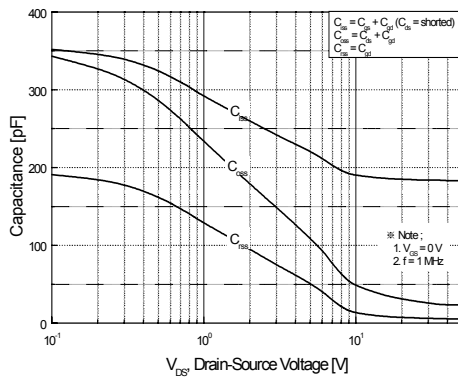


Figure 5. Capacitance Characteristics

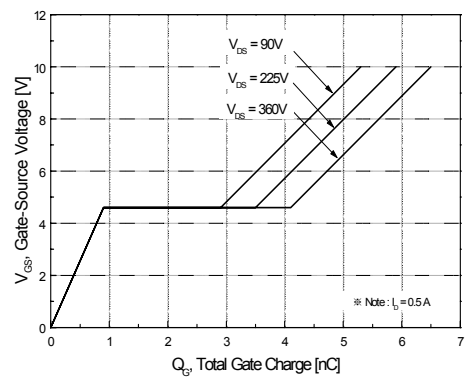


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

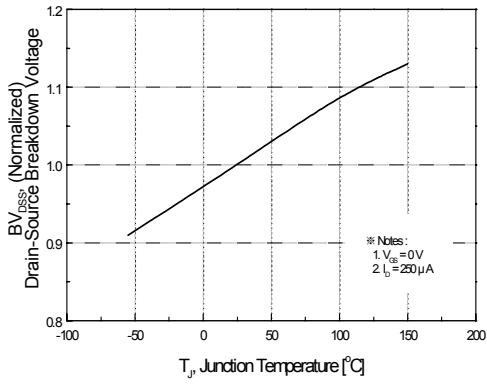


Figure 7. Breakdown Voltage Variation vs. Temperature

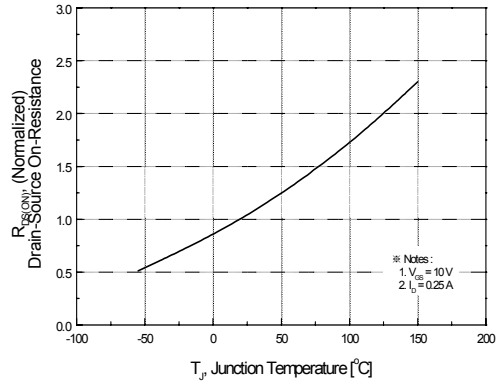


Figure 8. On-Resistance Variation vs. Temperature

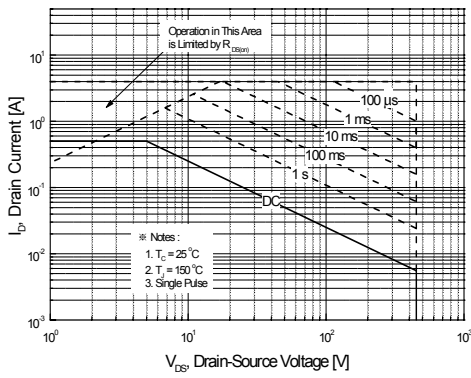


Figure 9. Maximum Safe Operating Area

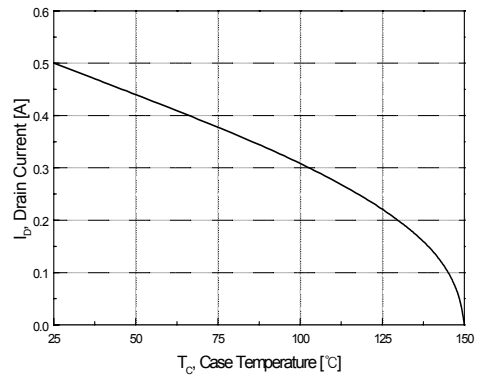


Figure 10. Maximum Drain Current vs. Case Temperature

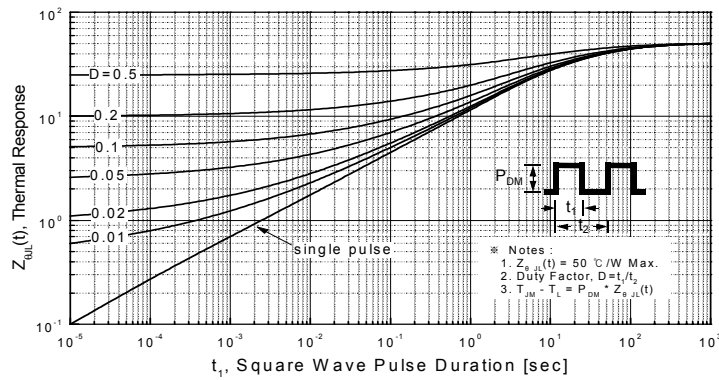
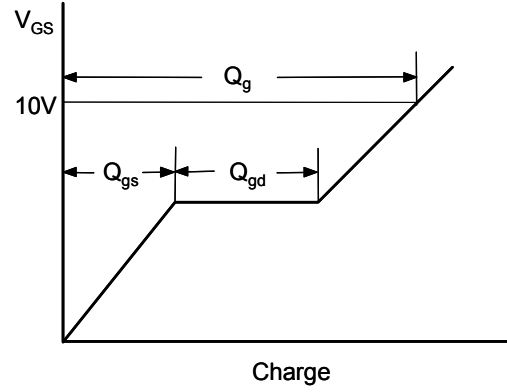
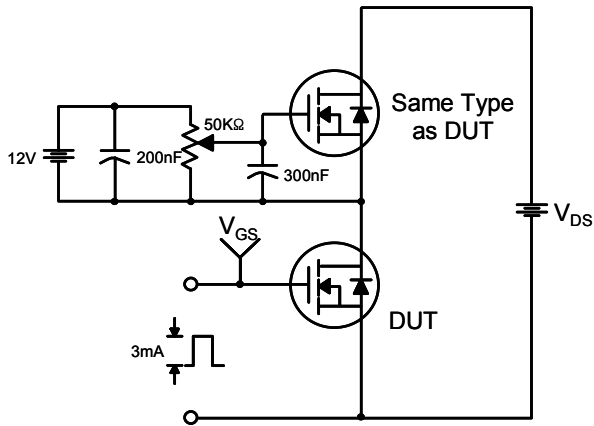
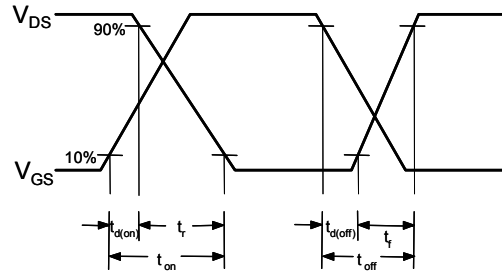
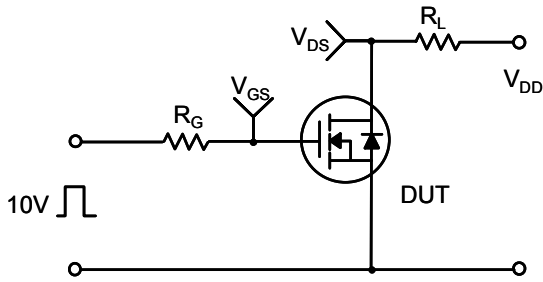


Figure 11. Transient Thermal Response Curve

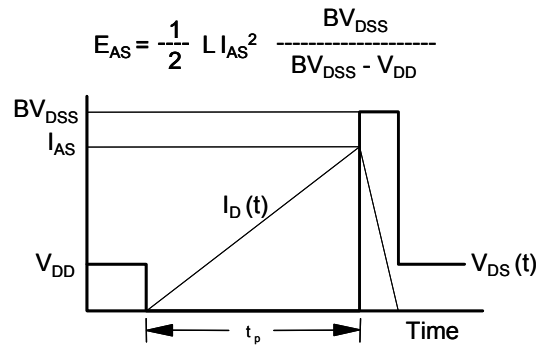
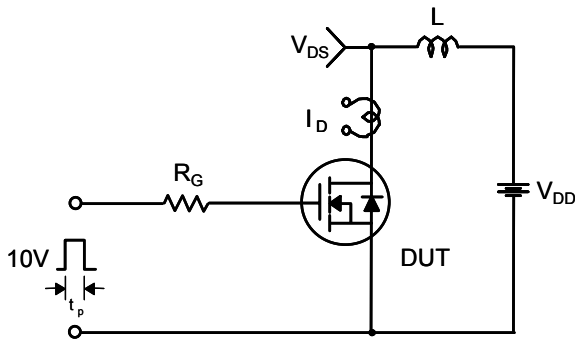
Gate Charge Test Circuit & Waveform



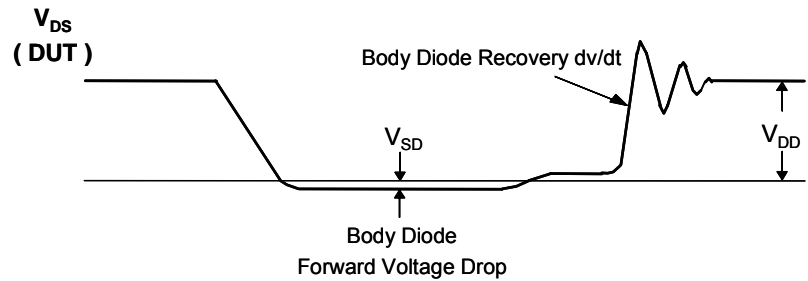
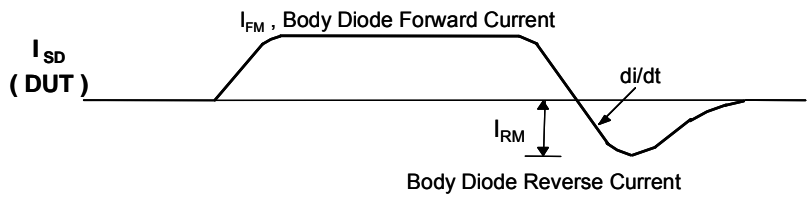
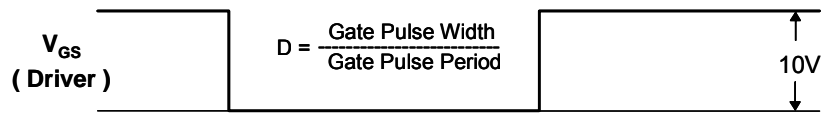
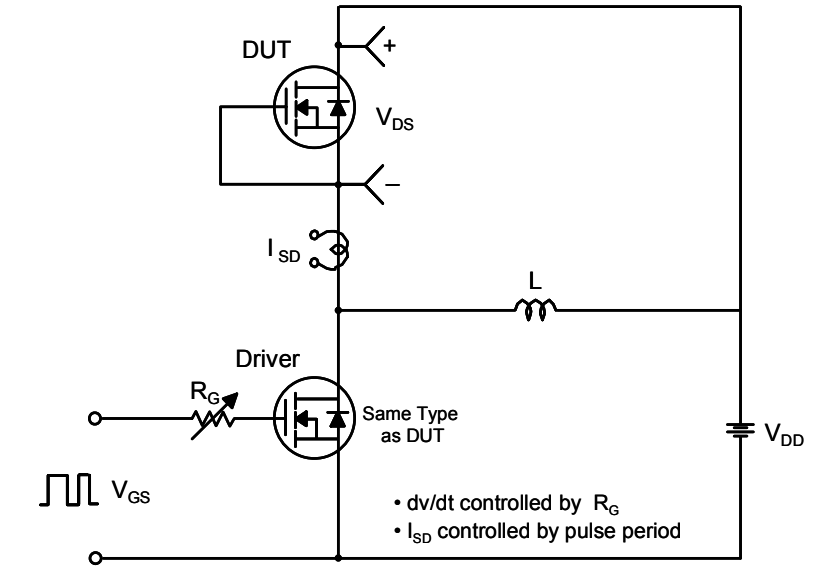
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



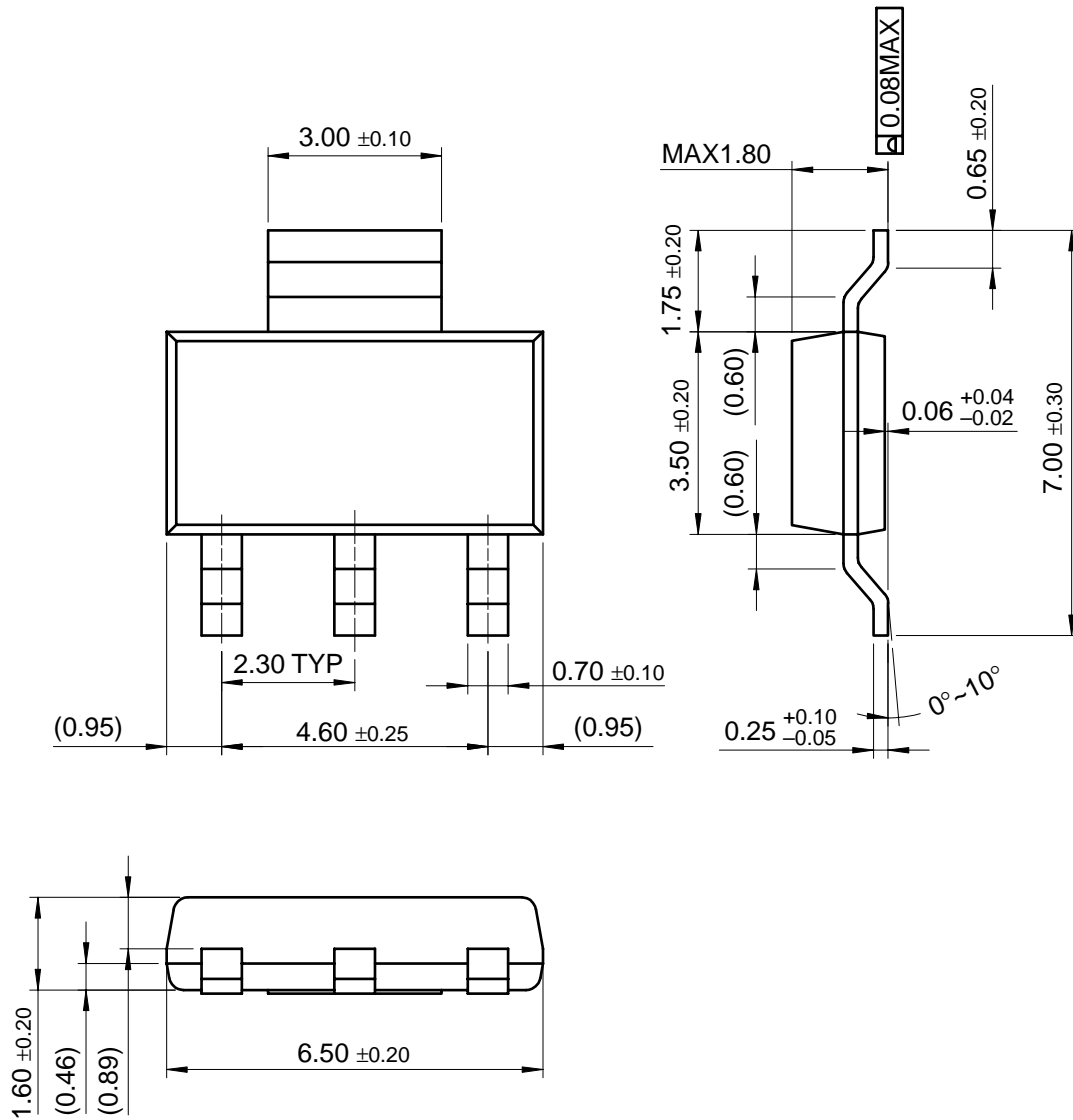
Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## SOT-223

SSM1N45B



Dimensions in Millimeters

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DOME™	GTO™	MICROWIRE™	QT Optoelectronics™	TinyLogic®
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EnSigna™	<i>i-Lo</i> ™	OCX™	RapidConnect™	UHC™
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